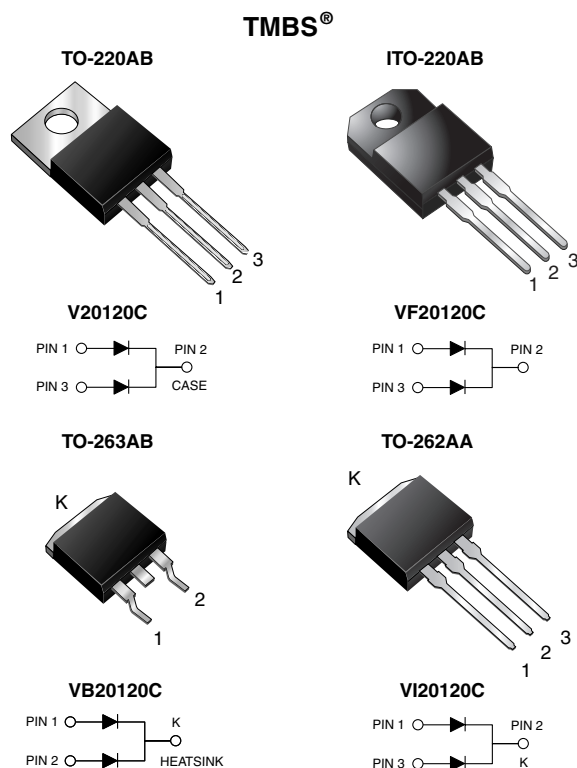




V20120C, VF20120C, VB20120C & VI20120C

Vishay General Semiconductor

Dual High-Voltage Trench MOS Barrier Schottky Rectifier

Ultra Low $V_F = 0.54 \text{ V}$ at $I_F = 5 \text{ A}$ 

FEATURES

- Trench MOS Schottky technology
- Low forward voltage drop, low power losses
- High efficiency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder bath temperature 275 °C maximum, 10 s, per JESD 22-B106 (for TO-220AB, ITO-220AB and TO-262AA package)
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

RoHS
COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB and TO-262AA

Molding compound meets UL 94 V-0 flammability rating

Base P/N-E3 - RoHS compliant, commercial grade

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

E3 suffix meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	2 x 10 A
V_{RRM}	120 V
I_{FSM}	120 A
V_F at $I_F = 10 \text{ A}$	0.64 V
$T_J \text{ max.}$	150 °C

MAXIMUM RATINGS ($T_A = 25 \text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	V20120C	VF20120C	VB20120C	VI20120C	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	120				V
Maximum average forward rectified current (fig. 1) per device per diode	$I_{F(AV)}$	20 10				A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	120				A
Non-repetitive avalanche energy at $T_J = 25 \text{ °C}$, $L = 60 \text{ mH}$ per diode	E_{AS}	80				mJ
Peak repetitive reverse current at $t_p = 2 \text{ } \mu\text{s}$, 1 kHz, $T_J = 38 \text{ °C} \pm 2 \text{ °C}$ per diode	I_{RRM}	0.5				A
Voltage rate of change (rated V_R)	dV/dt	10 000				V/ μs
Isolation voltage (ITO-220AB only) from terminal to heatsink $t = 1 \text{ min}$	V_{AC}	1500				V
Operating junction and storage temperature range	T_J, T_{STG}	- 40 to + 150				°C

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ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Breakdown voltage	$I_R = 1.0\text{ mA}$	$T_A = 25\text{ }^{\circ}\text{C}$	V_{BR}	120 (minimum)	-	V
Instantaneous forward voltage per diode ⁽¹⁾	$I_F = 5\text{ A}$	$T_A = 25\text{ }^{\circ}\text{C}$	V_F	0.62	-	V
	$I_F = 10\text{ A}$	$T_A = 25\text{ }^{\circ}\text{C}$		0.81	0.90	
	$I_F = 5\text{ A}$	$T_A = 125\text{ }^{\circ}\text{C}$		0.54	-	
	$I_F = 10\text{ A}$	$T_A = 125\text{ }^{\circ}\text{C}$		0.64	0.72	
Reverse current per diode ⁽²⁾	$V_R = 90\text{ V}$	$T_A = 25\text{ }^{\circ}\text{C}$ $T_A = 125\text{ }^{\circ}\text{C}$	I_R	8 6	- -	μA mA
	$V_R = 120\text{ V}$	$T_A = 25\text{ }^{\circ}\text{C}$ $T_A = 125\text{ }^{\circ}\text{C}$		- 14	700 45	μA mA

Notes

⁽¹⁾ Pulse test: 300 μs pulse width, 1 % duty cycle⁽²⁾ Pulse test: Pulse width $\leq 40\text{ ms}$

THERMAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)						
PARAMETER	SYMBOL	V20120C	VF20120C	VB20120C	VI20120C	UNIT
Typical thermal resistance per diode	$R_{\theta JC}$	2.8	5.0	2.8	2.8	$^{\circ}\text{C/W}$

ORDERING INFORMATION (Example)						
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE	
TO-220AB	V20120C-E3/4W	1.88	— 4W	50/tube	Tube	
ITO-220AB	VF20120C-E3/4W	1.75	4W	50/tube	Tube	
TO-263AB	VB20120C-E3/4W	1.37	4W	50/tube	Tube	
TO-263AB	VB20120C-E3/8W	1.37	8W	800/reel	Tape and reel	
TO-262AA	VI20120C-E3/4W	1.45	4W	50/tube	Tube	

RATINGS AND CHARACTERISTICS CURVES

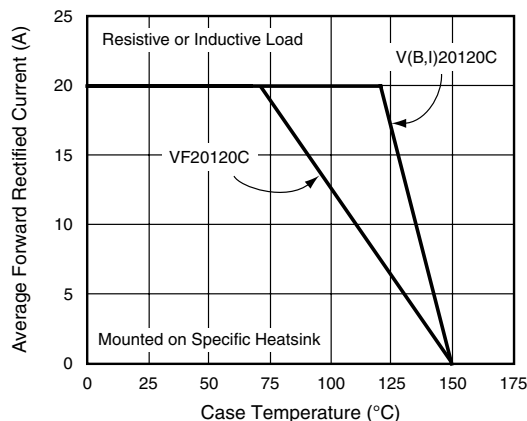
 $(T_A = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Figure 1. Maximum Forward Current Derating Curve

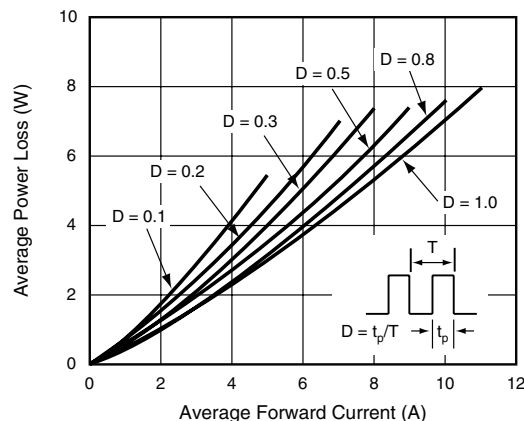


Figure 2. Forward Power Loss Characteristics Per Diode

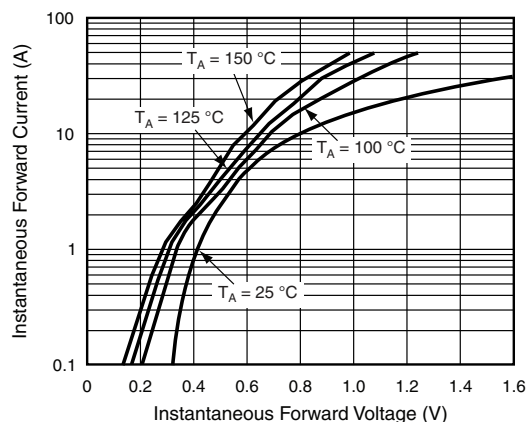


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

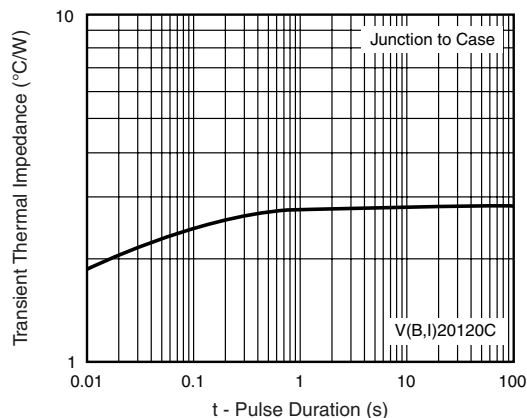


Figure 6. Typical Transient Thermal Impedance Per Diode

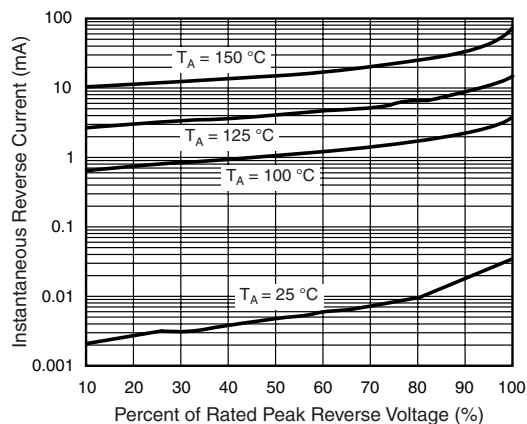


Figure 4. Typical Reverse Characteristics Per Diode

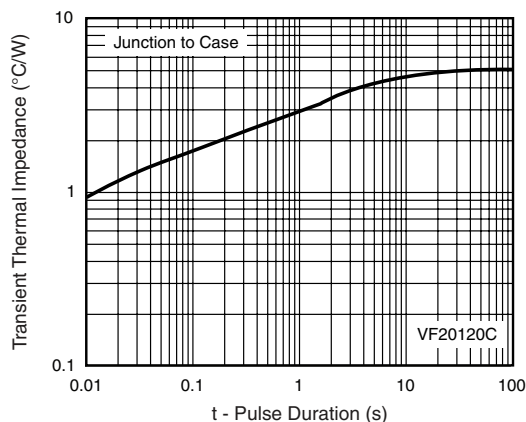


Figure 7. Typical Transient Thermal Impedance Per Diode

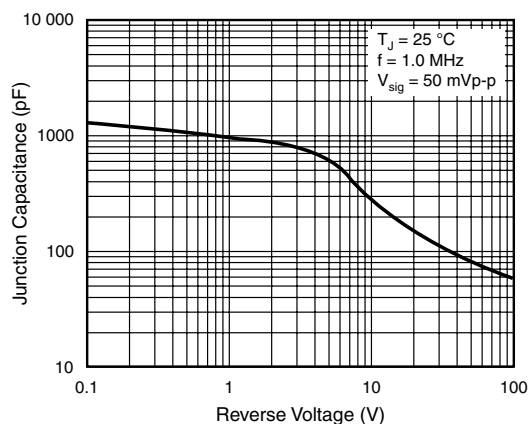


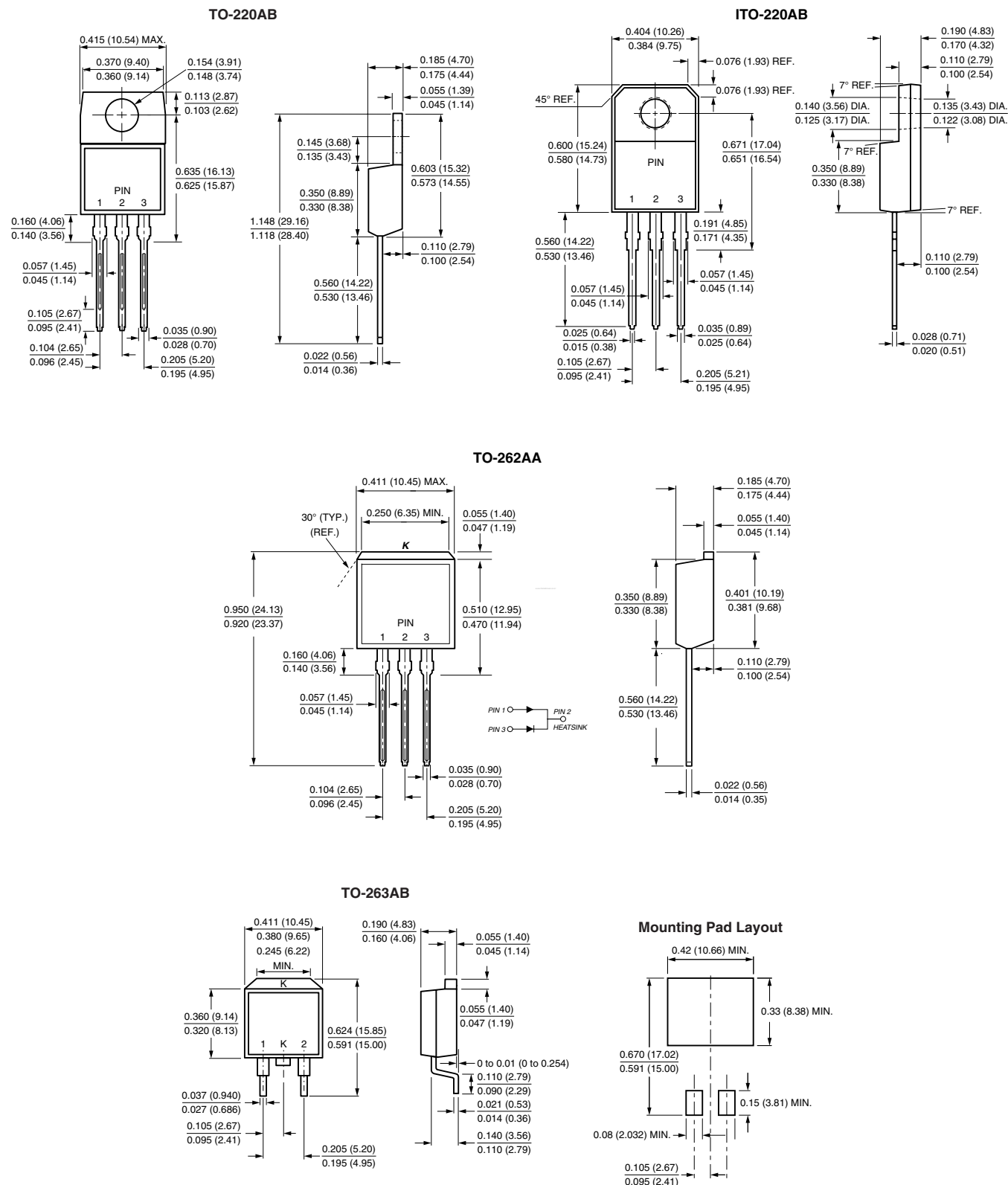
Figure 5. Typical Junction Capacitance Per Diode

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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)





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